

165-Bump BGA
Commercial Temp
Industrial Temp

72Mb SigmaDDR-II Burst of 2 ECCRAM™

300 MHz–167 MHz
1.8 V V_{DD}
1.8 V and 1.5 V V_{DDQ}

Features

- On-Chip ECC with virtually zero SER
- Simultaneous Read and Write SigmaDDR™ Interface
- Common I/O bus
- JEDEC-standard pinout and package
- Double Data Rate interface
- Limited Byte Write Capability due to ECC
- Burst of 2 Read and Write
- 1.8 V +100/–100 mV core power supply
- 1.5 V or 1.8 V HSTL Interface
- Pipelined read operation with self-timed Late Write
- Fully coherent read and write pipelines
- ZQ pin for programmable output drive strength
- IEEE 1149.1 JTAG-compliant Boundary Scan
- Pin-compatible with present 9Mb, 18Mb, 36Mb and 144Mb devices
- 165-bump, 15 mm x 17 mm, 1 mm bump pitch BGA package
- RoHS-compliant 165-bump BGA package available

SigmaDDR™ Family Overview

The GS8672T18/36AE SigmaDDR-II ECCRAMs are built in compliance with the SigmaDDR-II SRAM pinout standard for Common I/O synchronous SRAMs. They are 75,497,472-bit (72Mb) SRAMs. The GS8672T18/36AE SigmaDDR-II SRAMs are just one element in a family of low power, low voltage HSTL I/O SRAMs designed to operate at the speeds needed to implement economical high performance networking systems.

However, due to the On-Chip Error Correction (ECC), the Byte Write capability in ECCRAMs is not fully compatible with that in other SigmaDDR-II SRAMs. See the **Byte Write Control** section for further information.

Clocking and Addressing Schemes

The GS8672T18/36AE SigmaDDR-II SRAMs are synchronous devices. They employ two input register clock inputs, K and \bar{K} . K and \bar{K} are independent single-ended clock inputs, not differential inputs to a single differential clock input buffer. The device also allows the user to manipulate the output register clock inputs quasi independently with the C and \bar{C} clock inputs. C and \bar{C} are also independent single-ended clock inputs, not differential inputs. If the C clocks are tied high, the K clocks are routed internally to fire the output registers instead.

Common I/O x36 and x18 SigmaDDR-II ECCRAMs always transfer data in two packets. When a new address is loaded, A0 presets an internal 1-bit address counter. The counter increments by 1 (toggles) for each beat of a burst of two data transfer.

On-Chip Error Correction Code

GSI's ECCRAMs implement an ECC algorithm that detects and corrects all single-bit memory errors, including those induced by Soft Error Rate (SER) events such as cosmic rays, alpha particles etc. The resulting SER of these devices is anticipated to be <0.002 FITs/Mb — a 5-order-of-magnitude improvement over comparable SRAMs with no On-Chip ECC, which typically have an SER of 200 FITs/Mb or more. SER quoted above is based on reading taken at sea level.

Parameter Synopsis

| | -300 | -250 | -200 | -167 |
|-------|---------|---------|---------|--------|
| tKHKH | 3.3 ns | 4.0 ns | 5.0 ns | 6.0 ns |
| tKHQV | 0.45 ns | 0.45 ns | 0.45 ns | 0.5 ns |

2M x 36 SigmaDDR-II SRAM—Top View

| | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 |
|---|--------------------------|-------------------------|-------------------------|--------------------------------|-------------------------|------------------------|-------------------------|-------------------------|-------------------------|-------------------------|------|
| A | $\overline{\text{CQ}}$ | NF (144Mb) | SA | $\text{R}/\overline{\text{W}}$ | $\overline{\text{BW2}}$ | $\overline{\text{K}}$ | $\overline{\text{BW1}}$ | $\overline{\text{LD}}$ | SA | SA | CQ |
| B | NC | DQ27 | DQ18 | SA | $\overline{\text{BW3}}$ | K | $\overline{\text{BW0}}$ | SA | NC | NC | DQ8 |
| C | NC | NC | DQ28 | V_{SS} | SA | SA0 | SA | V_{SS} | NC | DQ17 | DQ7 |
| D | NC | DQ29 | DQ19 | V_{SS} | V_{SS} | V_{SS} | V_{SS} | V_{SS} | NC | NC | DQ16 |
| E | NC | NC | DQ20 | V_{DDQ} | V_{SS} | V_{SS} | V_{SS} | V_{DDQ} | NC | DQ15 | DQ6 |
| F | NC | DQ30 | DQ21 | V_{DDQ} | V_{DD} | V_{SS} | V_{DD} | V_{DDQ} | NC | NC | DQ5 |
| G | NC | DQ31 | DQ22 | V_{DDQ} | V_{DD} | V_{SS} | V_{DD} | V_{DDQ} | NC | NC | DQ14 |
| H | $\overline{\text{Doff}}$ | V_{REF} | V_{DDQ} | V_{DDQ} | V_{DD} | V_{SS} | V_{DD} | V_{DDQ} | V_{DDQ} | V_{REF} | ZQ |
| J | NC | NC | DQ32 | V_{DDQ} | V_{DD} | V_{SS} | V_{DD} | V_{DDQ} | NC | DQ13 | DQ4 |
| K | NC | NC | DQ23 | V_{DDQ} | V_{DD} | V_{SS} | V_{DD} | V_{DDQ} | NC | DQ12 | DQ3 |
| L | NC | DQ33 | DQ24 | V_{DDQ} | V_{SS} | V_{SS} | V_{SS} | V_{DDQ} | NC | NC | DQ2 |
| M | NC | NC | DQ34 | V_{SS} | V_{SS} | V_{SS} | V_{SS} | V_{SS} | NC | DQ11 | DQ1 |
| N | NC | DQ35 | DQ25 | V_{SS} | SA | SA | SA | V_{SS} | NC | NC | DQ10 |
| P | NC | NC | DQ26 | SA | SA | C | SA | SA | NC | DQ9 | DQ0 |
| R | TDO | TCK | SA | SA | SA | $\overline{\text{C}}$ | SA | SA | SA | TMS | TDI |

11 x 15 Bump BGA—13 x 15 mm² Body—1 mm Bump Pitch

Notes:

1. $\overline{\text{BW0}}$ controls writes to DQ0:DQ8; $\overline{\text{BW1}}$ controls writes to DQ9:DQ17; $\overline{\text{BW2}}$ controls writes to DQ18:DQ26; $\overline{\text{BW3}}$ controls writes to DQ27:DQ35.

4M x 18 SigmaDDR-II SRAM—Top View

| | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 |
|---|------|------------------|------------------|------------------|-----------------|-----------------|-----------------|------------------|------------------|------------------|-----|
| A | CQ | SA | SA | R/W | BW1 | K | NF | LD | SA | SA | CQ |
| B | NC | DQ9 | NF | SA | NF | K | BW0 | SA | NC | NC | DQ8 |
| C | NC | NC | NF | V _{SS} | SA | SA0 | SA | V _{SS} | NC | DQ7 | NF |
| D | NC | NF | DQ10 | V _{SS} | V _{SS} | V _{SS} | V _{SS} | V _{SS} | NC | NC | NF |
| E | NC | NC | DQ11 | V _{DDQ} | V _{SS} | V _{SS} | V _{SS} | V _{DDQ} | NC | NF | DQ6 |
| F | NC | DQ12 | NF | V _{DDQ} | V _{DD} | V _{SS} | V _{DD} | V _{DDQ} | NC | NC | DQ5 |
| G | NC | NF | DQ13 | V _{DDQ} | V _{DD} | V _{SS} | V _{DD} | V _{DDQ} | NC | NC | NF |
| H | Doff | V _{REF} | V _{DDQ} | V _{DDQ} | V _{DD} | V _{SS} | V _{DD} | V _{DDQ} | V _{DDQ} | V _{REF} | ZQ |
| J | NC | NC | NF | V _{DDQ} | V _{DD} | V _{SS} | V _{DD} | V _{DDQ} | NC | DQ4 | NF |
| K | NC | NC | DQ14 | V _{DDQ} | V _{DD} | V _{SS} | V _{DD} | V _{DDQ} | NC | NF | DQ3 |
| L | NC | DQ15 | NF | V _{DDQ} | V _{SS} | V _{SS} | V _{SS} | V _{DDQ} | NC | NC | DQ2 |
| M | NC | NC | NF | V _{SS} | V _{SS} | V _{SS} | V _{SS} | V _{SS} | NC | DQ1 | NF |
| N | NC | NF | DQ16 | V _{SS} | SA | SA | SA | V _{SS} | NC | NC | NF |
| P | NC | NC | DQ17 | SA | SA | C | SA | SA | NC | NF | DQ0 |
| R | TDO | TCK | SA | SA | SA | C | SA | SA | SA | TMS | TDI |

11 x 15 Bump BGA—13 x 15 mm² Body—1 mm Bump Pitch

Notes:

1. BW0 controls writes to DQ0:DQ8; BW1 controls writes to DQ9:DQ17.

Pin Description Table

| Symbol | Description | Type | Comments |
|--------------------------|---------------------------------|--------------|------------------------|
| SA | Synchronous Address Inputs | Input | — |
| R/W | Synchronous Read/Write | Input | — |
| BW0–BW3 | Synchronous Byte Writes | Input | Active Low |
| LD | Synchronous Load Pin | Input | Active Low |
| K | Input Clock | Input | Active High |
| \bar{K} | Input Clock | Input | Active Low |
| C | Output Clock | Input | Active High |
| \bar{C} | Output Clock | Input | Active Low |
| TMS | Test Mode Select | Input | — |
| TDI | Test Data Input | Input | — |
| TCK | Test Clock Input | Input | — |
| TDO | Test Data Output | Output | — |
| V _{REF} | HSTL Input Reference Voltage | Input | — |
| ZQ | Output Impedance Matching Input | Input | — |
| MCL | Must Connect Low | — | — |
| DQ | Data I/O | Input/Output | Three State |
| $\overline{\text{Doff}}$ | Disable DLL when low | Input | Active Low |
| CQ | Output Echo Clock | Output | — |
| \bar{CQ} | Output Echo Clock | Output | — |
| V _{DD} | Power Supply | Supply | 1.8 V Nominal |
| V _{DDQ} | Isolated Output Buffer Supply | Supply | 1.8 V or 1.5 V Nominal |
| V _{SS} | Power Supply: Ground | Supply | — |
| NC | No Connect | — | — |
| NF | No Function | — | — |

Notes:

1. NC = Not Connected to die or any other pin
2. NF = No Function. There is an electrical connection to this input pin, but the signal has no function in the device. It can be left unconnected, or tied to V_{SS} or V_{DDQ}.
3. C, \bar{C} , K, or \bar{K} cannot be set to V_{REF} voltage.

Background

Common I/O SRAMs, from a system architecture point of view, are attractive in read dominated or block transfer applications. Therefore, the SigmaDDR-II ECCRAM interface and truth table are optimized for burst reads and writes. Common I/O SRAMs are unpopular in applications where alternating reads and writes are needed because bus turnaround delays can cut high speed Common I/O SRAM data bandwidth in half.

Burst Operations

Read and write operations are "burst" operations. In every case where a read or write command is accepted by the ECCRAM, it will respond by issuing or accepting two beats of data, executing a data transfer on subsequent rising edges of K and \overline{K} , as illustrated in the timing diagrams. It is not possible to stop a burst once it starts. Two beats of data are always transferred. This means that it is possible to load new addresses every K clock cycle. Addresses can be loaded less often, if intervening deselect cycles are inserted.

Deselect Cycles

Chip Deselect commands are pipelined to the same degree as read commands. This means that if a deselect command is applied to the ECCRAM on the next cycle after a read command captured by the ECCRAM, the device will complete the two beat read data transfer and then execute the deselect command, returning the output drivers to high-Z. A high on the \overline{LD} pin prevents the RAM from loading read or write command inputs and puts the RAM into deselect mode as soon as it completes all outstanding burst transfer operations.

SigmaDDR-II ECCRAM Read Cycles

The SRAM executes pipelined reads. The status of the Address, \overline{LD} and R/\overline{W} pins are evaluated on the rising edge of K. The read command (\overline{LD} low and R/\overline{W} high) is clocked into the SRAM by a rising edge of K. After the next rising edge of K, the SRAM produces data out in response to the next rising edge of \overline{C} (or the next rising edge of \overline{K} , if C and \overline{C} are tied high). The second beat of data is transferred on the next rising edge of C, for a total of two transfers per address load.

SigmaDDR-II ECCRAM Write Cycles

The status of the Address, \overline{LD} and R/\overline{W} pins are evaluated on the rising edge of K. The ECCRAM executes "late write" data transfers. Data in is due at the device inputs on the rising edge of K following the rising edge of K clock used to clock in the write command (\overline{LD} and R/\overline{W} low) and the write address. To complete the remaining beat of the burst of two write transfer, the ECCRAM captures data in on the next rising edge of \overline{K} , for a total of two transfers per address load.

Power-Up Sequence for SigmaDDR-II ECCRAMs

SigmaDDR-II ECCRAMs must be powered up in a specific sequence in order to avoid undefined operations.

Power-Up Sequence

1. Power-up and maintain $\overline{\text{Doff}}$ at low state.
 - 1a. Apply V_{DD} .
 - 1b. Apply V_{DDQ} .
 - 1c. Apply V_{REF} (may also be applied at the same time as V_{DDQ}).
2. After power is achieved and clocks (K, \overline{K} , C, \overline{C}) are stabilized, 163,840 cycles are required to set Output Driver Impedance.
3. Change $\overline{\text{Doff}}$ to High. An additional 65,536 clock cycles are required to lock the DLL after it has been enabled.

Note:

The DLL may be reset by driving the $\overline{\text{Doff}}$ pin low or by stopping the K clocks for at least 30 ns. 65,536 cycles of clean K clocks are always required to re-lock the DLL after reset.

DLL Constraints

- The DLL synchronizes to either K or C clock. These clocks should have low phase jitter ($t_{KCV\text{ar}}$).
- The DLL cannot operate at a frequency lower than that specified by the $t_{KH\text{KH}}$ maximum specification for the desired operating clock frequency.
- If the incoming clock is not stabilized when DLL is enabled, the DLL may lock on the wrong frequency and cause undefined errors or failures during the initial stage.

Note:

If the frequency is changed, DLL reset is required. After reset, a minimum of 65,536 cycles is required for DLL lock.

On-Chip Error Correction

SigmaDDR-II ECCRAMs implement a single-bit error detection and correction algorithm (specifically, a Hamming Code) on each DDR data word (comprising two 9-bit data bytes) transmitted on each 9-bit data bus (i.e., transmitted on D/Q[8:0], D/Q[17:9], D/Q[26:18], or D/Q[35:27]). To accomplish this, 5 ECC parity bits (invisible to the user) are utilized per every 18 data bits (visible to the user).

The ECC algorithm neither corrects nor detects multi-bit errors. However, GSI ECCRAMs are architected in such a way that a single SER event very rarely causes a multi-bit error across any given "transmitted data unit", where a "transmitted data unit" represents the data transmitted as the result of a single read or write operation to a particular address. The extreme rarity of multi-bit errors results in the SER mentioned previously (i.e., <0.002 FITs/Mb measured at sea level.)

Not only does the on-chip ECC significantly improve SER performance, but it also frees up the entire memory array for data storage. Very often SRAM applications allocate 1/9th of the memory array (i.e., one "error bit" per eight "data bits", in any 9-bit "data byte") for error detection (either simple parity error detection, or system-level ECC error detection and correction). Such error-bit allocation is unnecessary with ECCRAMs the entire memory array can be utilized for data storage, effectively providing 12.5% greater storage capacity compared to SRAMs of the same density not equipped with on-chip ECC.

Output Register Control

SigmaDDR-II ECCRAMs offer two mechanisms for controlling the output data registers. Typically, control is handled by the Output Register Clock inputs, C and \overline{C} . The Output Register Clock inputs can be used to make small phase adjustments in the firing of the output registers by allowing the user to delay driving data out as much as a few nanoseconds beyond the next rising edges of the K and \overline{K} clocks. If the C and \overline{C} clock inputs are tied high, the RAM reverts to K and \overline{K} control of the outputs, allowing the RAM to function as a conventional pipelined read ECCRAM.

Special Functions

Byte Write Control

Byte Write Enable pins are sampled at the same time that Data In is sampled. A High on the Byte Write Enable pin associated with a particular byte (e.g., $\overline{BW}0$ controls D0–D8 inputs) will inhibit the storage of that particular byte, leaving whatever data may be stored at the current address at that byte location undisturbed. Any or all of the Byte Write Enable pins may be driven High or Low during the data in sample times in a write sequence (with some restrictions—see below).

Each write enable command and write address loaded into the RAM provides the base address for a 2-beat data transfer. The x18 version of the RAM, for example, may write 36 bits in association with each address loaded.

The Byte Write Enable pins were originally defined to be DDR inputs, so they could be used to enable/block the storage of each byte of DDR write data transmitted on their corresponding 9-bit data busses during write operations. However, because ECCRAMs implement ECC across entire DDR data words (i.e., across 18-bits of data), "Half Write" operations (i.e., write operations in which a $\overline{BW}n$ pin is asserted for only half of a DDR write data transfer on the associated 9bit data bus) are not supported in these devices. Only "Full Write" operations (i.e., write operations in which a $\overline{BW}n$ pin is asserted for both halves of a DDR write data transfer on the associated 9-bit data bus) and "Abort Write" operations" (i.e., write operations in which a $\overline{BW}n$ pin is de-asserted for both halves of a DDR write data transfer on the associated 9-bit data bus) are supported.

If a Half Write operation is initiated on a particular 9-bit data bus, the ECC bits associated with the corresponding DDR data word will be written incorrectly, causing subsequent reads from that address to return incorrect/corrupted data (multiple bits of both halves of data will be corrupted, regardless which half was to be written and which half was to remain unchanged).

Consequently, the Byte Write Enable pins available in ECCRAMs are actually quasiSDR inputs. That is, although they are sampled on the rising edges of both the positive (K) and negative (\overline{K}) input clocks, the values sampled must always be the same in any given clock cycle.

Byte Write Truth Table

The truth table below applies to write operations to Address "m", where Address "m" is the 18-bit memory location comprising the 2 beats of DDR write data associated with each $\overline{BW}n$ pin in a given clock cycle.

| $\overline{BW}n$ | | Input Data Byte n | | Operation | Allowed? | Result |
|--------------------------|-------------------------------------|--------------------------|-------------------------------------|------------|----------|---------------------|
| $\uparrow K$ (Beat 1) | $\uparrow \overline{K}$ (Beat 2) | $\uparrow K$ (Beat 1) | $\uparrow \overline{K}$ (Beat 2) | | | |
| 0 | 0 | D0 | D1 | Full Write | Yes | Address m = D0 + D1 |
| 0 | 1 | D0 | X | Half Write | No | Address m corrupted |
| 1 | 0 | X | D1 | Half Write | No | Address m corrupted |
| 1 | 1 | X | X | Abort | Yes | Address m unchanged |

Notes:

1. $\overline{BW}0$ is associated with Input Data Byte D[8:0].
2. $\overline{BW}1$ is associated with Input Data Byte D[17:9].
3. $\overline{BW}2$ is associated with Input Data Byte D[26:18] (in x36 only).
4. $\overline{BW}3$ is associated with Input Data Byte D[35:27] (in x36 only).

FLXDrive-II Output Driver Impedance Control

HSTL I/O SigmaDDR-II ECCRAMs are supplied with programmable impedance output drivers. The ZQ pin must be connected to V_{SS} via an external resistor, R_Q , to allow the ECCRAM to monitor and adjust its output driver impedance. The value of R_Q must be 5X the value of the desired RAM output impedance. The allowable range of R_Q to guarantee impedance matching continuously is between 175Ω and 275Ω . Periodic readjustment of the output driver impedance is necessary as the impedance is affected by drifts in supply voltage and temperature. The ECCRAM's output impedance circuitry compensates for drifts in supply voltage and temperature. A clock cycle counter periodically triggers an impedance evaluation, resets and counts again. Each impedance evaluation may move the output driver impedance level one step at a time towards the optimum level. The output driver is implemented with discrete binary weighted impedance steps.

Common I/O SigmaDDR-II ECCRAM Truth Table

| K_n | \overline{LD} | R/\overline{W} | DQ | | Operation |
|------------|-----------------|------------------|---|--------------------------------|-----------|
| | | | A + 0 | A + 1 | |
| \uparrow | 1 | X | Hi-Z | Hi-Z | Deselect |
| \uparrow | 0 | 0 | $D@K_{n+1}$ | $D@K_{n+1}$ | Write |
| \uparrow | 0 | 1 | $Q@K_{n+1}$ or \overline{C}_{n+1} | $Q@K_{n+2}$ or C_{n+2} | Read |

Note:

Q is controlled by K clocks if C clocks are not used.

Burst of 2 Byte Write Clock Truth Table

| \overline{BW} | \overline{BW} | Current Operation | D | D |
|-------------------------------|--|--|-------------------------------|---|
| $K \uparrow$ ($t_n + 1$) | $K \uparrow$ ($t_n + 1\frac{1}{2}$) | $K \uparrow$ (t_n) | $K \uparrow$ ($t_n + 1$) | $\overline{K} \uparrow$ ($t_n + 1\frac{1}{2}$) |
| T | T | Write Dx stored if $\overline{BW}_n = 0$ in both data transfers | D1 | D2 |
| T | F | Invalid- Operation Not Allowed | D1 | X |
| F | T | Invalid- Operation Not Allowed | X | D2 |
| F | F | Write Abort No Dx stored in either data transfer | X | X |

Notes:

- "1" = input "high"; "0" = input "low"; "X" = input "don't care"; "T" = input "true"; "F" = input "false".
- If one or more $\overline{BW}_n = 0$, then $\overline{BW} = "T"$, else $\overline{BW} = "F"$.

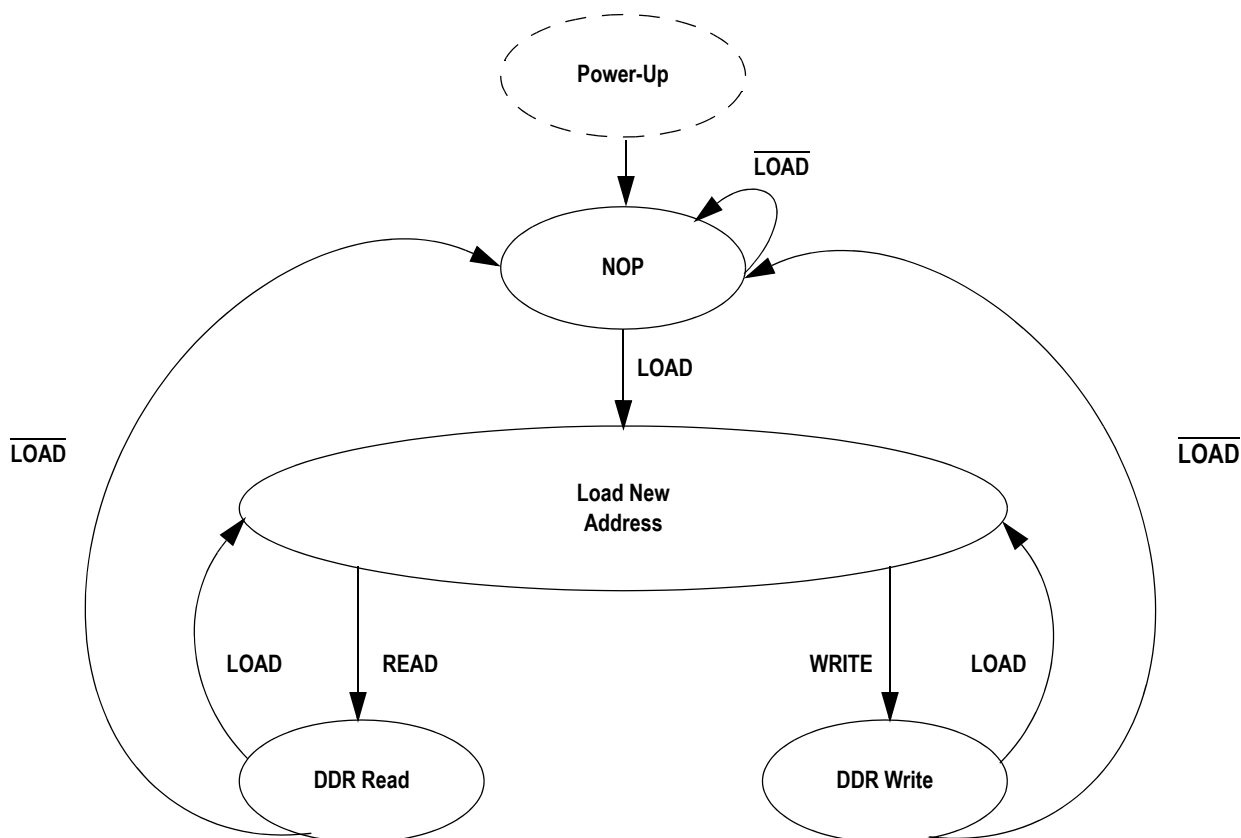
x36 Byte Write Enable (\overline{BWn}) Truth Table

| $\overline{BW0}$ | $\overline{BW1}$ | $\overline{BW2}$ | $\overline{BW3}$ | D0–D8 | D9–D17 | D18–D26 | D27–D35 |
|------------------|------------------|------------------|------------------|------------|------------|------------|------------|
| 1 | 1 | 1 | 1 | Don't Care | Don't Care | Don't Care | Don't Care |
| 0 | 1 | 1 | 1 | Data In | Don't Care | Don't Care | Don't Care |
| 1 | 0 | 1 | 1 | Don't Care | Data In | Don't Care | Don't Care |
| 0 | 0 | 1 | 1 | Data In | Data In | Don't Care | Don't Care |
| 1 | 1 | 0 | 1 | Don't Care | Don't Care | Data In | Don't Care |
| 0 | 1 | 0 | 1 | Data In | Don't Care | Data In | Don't Care |
| 1 | 0 | 0 | 1 | Don't Care | Data In | Data In | Don't Care |
| 0 | 0 | 0 | 1 | Data In | Data In | Data In | Don't Care |
| 1 | 1 | 1 | 0 | Don't Care | Don't Care | Don't Care | Data In |
| 0 | 1 | 1 | 0 | Data In | Don't Care | Don't Care | Data In |
| 1 | 0 | 1 | 0 | Don't Care | Data In | Don't Care | Data In |
| 0 | 0 | 1 | 0 | Data In | Data In | Don't Care | Data In |
| 1 | 1 | 0 | 0 | Don't Care | Don't Care | Data In | Data In |
| 0 | 1 | 0 | 0 | Data In | Don't Care | Data In | Data In |
| 1 | 0 | 0 | 0 | Don't Care | Data In | Data In | Data In |
| 0 | 0 | 0 | 0 | Data In | Data In | Data In | Data In |

x18 Byte Write Enable (\overline{BWn}) Truth Table

| $\overline{BW0}$ | $\overline{BW1}$ | D0–D8 | D9–D17 |
|------------------|------------------|------------|------------|
| 1 | 1 | Don't Care | Don't Care |
| 0 | 1 | Data In | Don't Care |
| 1 | 0 | Don't Care | Data In |
| 0 | 0 | Data In | Data In |

B2 State Diagram



Notes:

1. The internal address burst counter is a 1 bit counter (i.e., when first address is A0, next internal burst address is A0+1).
2. "READ" refers to read active status with R/\overline{W} = High, "WRITE" refers to write inactive status with R/\overline{W} = Low.
3. "LOAD" refers to read new address active status with \overline{LD} = Low, "LOAD" refers to read new address inactive status with \overline{LD} = High.

Absolute Maximum Ratings

(All voltages reference to V_{SS})

| Symbol | Description | Value | Unit |
|-----------|-------------------------------|--|--------------------|
| V_{DD} | Voltage on V_{DD} Pins | -0.5 to 2.4 | V |
| V_{DDQ} | Voltage in V_{DDQ} Pins | -0.5 to V_{DD} | V |
| V_{REF} | Voltage in V_{REF} Pins | -0.5 to V_{DDQ} | V |
| $V_{I/O}$ | Voltage on I/O Pins | -0.5 to $V_{DDQ} + 0.5$ (≤ 2.4 V max.) | V |
| V_{IN} | Voltage on Other Input Pins | -0.5 to $V_{DDQ} + 0.5$ (≤ 2.4 V max.) | V |
| I_{IN} | Input Current on Any Pin | +/-100 | mA dc |
| I_{OUT} | Output Current on Any I/O Pin | +/-100 | mA dc |
| T_J | Maximum Junction Temperature | 125 | $^{\circ}\text{C}$ |
| T_{STG} | Storage Temperature | -55 to 125 | $^{\circ}\text{C}$ |

Note:

Permanent damage to the device may occur if the Absolute Maximum Ratings are exceeded. Operation should be restricted to Recommended Operating Conditions. Exposure to conditions exceeding the Recommended Operating Conditions, for an extended period of time, may affect reliability of this component.

Recommended Operating Conditions

Power Supplies

| Parameter | Symbol | Min. | Typ. | Max. | Unit |
|--------------------|-----------|--------------------|------|--------------------|------|
| Supply Voltage | V_{DD} | 1.7 | 1.8 | 1.9 | V |
| I/O Supply Voltage | V_{DDQ} | 1.4 | — | V_{DD} | V |
| Reference Voltage | V_{REF} | $V_{DDQ}/2 - 0.05$ | — | $V_{DDQ}/2 + 0.05$ | V |

Note:

The power supplies need to be powered up simultaneously or in the following sequence: V_{DD} , V_{DDQ} , V_{REF} , followed by signal inputs. The power down sequence must be the reverse. V_{DDQ} must not exceed V_{DD} .

Operating Temperature

| Parameter | Symbol | Min. | Typ. | Max. | Unit |
|--|--------|------|------|------|--------------------|
| Ambient Temperature (Commercial Range Versions) | T_A | 0 | 25 | 70 | $^{\circ}\text{C}$ |
| Ambient Temperature (Industrial Range Versions) | T_A | -40 | 25 | 85 | $^{\circ}\text{C}$ |

HSTL I/O DC Input Characteristics

| Parameter | Symbol | Min | Max | Units | Notes |
|---------------------|---------------|-----------------|-------------------|-------|-------|
| DC Input Logic High | $V_{IH} (dc)$ | $V_{REF} + 0.1$ | $V_{DDQ} + 0.3 V$ | V | 1 |
| DC Input Logic Low | $V_{IL} (dc)$ | $-0.3 V$ | $V_{REF} - 0.1$ | V | 1 |

Notes:

- Compatible with both 1.8 V and 1.5 V I/O drivers.
- These are DC test criteria. DC design criteria is $V_{REF} \pm 50$ mV. The AC V_{IH}/V_{IL} levels are defined separately for measuring timing parameters.
- $V_{IL} (Min)$ DC = $-0.3 V$, $V_{IL} (Min)$ AC = $-1.5 V$ (pulse width ≤ 3 ns).
- $V_{IH} (Max)$ DC = $V_{DDQ} + 0.3 V$, $V_{IH} (Max)$ AC = $V_{DDQ} + 0.85 V$ (pulse width ≤ 3 ns).

HSTL I/O AC Input Characteristics

| Parameter | Symbol | Min | Max | Units | Notes |
|-----------------------------------|----------------|-----------------|-------------------|-------|-------|
| AC Input Logic High | $V_{IH} (ac)$ | $V_{REF} + 0.2$ | — | V | 2,3 |
| AC Input Logic Low | $V_{IL} (ac)$ | — | $V_{REF} - 0.2$ | V | 2,3 |
| V_{REF} Peak-to-Peak AC Voltage | $V_{REF} (ac)$ | — | 5% $V_{REF} (DC)$ | V | 1 |

Notes:

- The peak-to-peak AC component superimposed on V_{REF} may not exceed 5% of the DC component of V_{REF} .
- To guarantee AC characteristics, V_{IH} , V_{IL} , T_{rise} , and T_{fall} of inputs and clocks must be within 10% of each other.
- For devices supplied with HSTL I/O input buffers. Compatible with both 1.8 V and 1.5 V I/O drivers.

Capacitance

($T_A = 25^\circ C$, $f = 1$ MHz, $V_{DD} = 1.8 V$)

| Parameter | Symbol | Test conditions | Typ. | Max. | Unit |
|--------------------|-----------|-----------------|------|------|------|
| Input Capacitance | C_{IN} | $V_{IN} = 0 V$ | 4 | 5 | pF |
| Output Capacitance | C_{OUT} | $V_{OUT} = 0 V$ | 4.5 | 5.5 | pF |

Note:

This parameter is sample tested.

*Assuming stable conditions, the RAM can achieve optimum impedance within 1024 cycles.

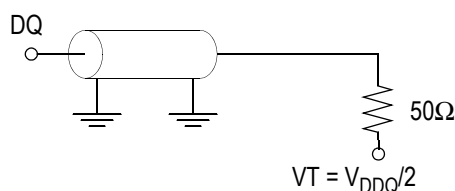
AC Test Conditions

| Parameter | Conditions |
|------------------------|-------------|
| Input high level | 1.25 V |
| Input low level | 0.25 V |
| Max. input slew rate | 2 V/ns |
| Input reference level | 0.75 |
| Output reference level | $V_{DDQ}/2$ |

Note:

Test conditions as specified with output loading as shown unless otherwise noted.

AC Test Load Diagram



$R_Q = 250\ \Omega$ (HSTL I/O)
 $V_{REF} = 0.75\ V$

Input and Output Leakage Characteristics

| Parameter | Symbol | Test Conditions | Min. | Max |
|---|----------------------------------|--|--------------------|-----------------|
| Input Leakage Current (except mode pins) | I_{IL} | $V_{IN} = 0\ \text{to}\ V_{DD}$ | -2 μA | 2 μA |
| $\overline{\text{Doff}}$ | $I_{IL\ \overline{\text{DOFF}}}$ | $V_{IN} = 0\ \text{to}\ V_{DD}$ | -100 μA | 2 μA |
| Output Leakage Current | I_{OL} | Output Disable, $V_{OUT} = 0\ \text{to}\ V_{DDQ}$ | -2 μA | 2 μA |

Programmable Impedance HSTL Output Driver DC Electrical Characteristics

| Parameter | Symbol | Min. | Max. | Units | Notes |
|-------------------------|-----------|--------------------|--------------------|----------|-------|
| Output High Voltage | V_{OH1} | $V_{DDQ}/2 - 0.12$ | $V_{DDQ}/2 + 0.12$ | V | 1 |
| Output Low Voltage | V_{OL1} | $V_{DDQ}/2 - 0.12$ | $V_{DDQ}/2 + 0.12$ | V | 2 |
| Output High Voltage | V_{OH2} | $V_{DDQ} - 0.2$ | V_{DDQ} | V | 3, 4 |
| Output Low Voltage | V_{OL2} | V_{SS} | 0.2 | V | 3, 5 |
| Output Driver Impedance | R_{OUT} | $(RQ/5) * 0.88$ | $(RQ/5) * 1.12$ | Ω | 6, 7 |

Notes:

- $I_{OH} = (V_{DDQ}/2) / (RQ/5) \pm 15\%$ @ $V_{OH} = V_{DDQ}/2$ (for: $175\Omega \leq RQ \leq 275\Omega$).
- $I_{OL} = (V_{DDQ}/2) / (RQ/5) \pm 15\%$ @ $V_{OL} = V_{DDQ}/2$ (for: $175\Omega \leq RQ \leq 275\Omega$).
- $0\Omega \leq RQ \leq \infty\Omega$
- $I_{OH} = -1.0$ mA
- $I_{OL} = 1.0$ mA
- Parameter applies when $175\Omega \leq RQ \leq 275\Omega$
- Tested at $V_{OUT} = V_{DDQ} * 0.2$ and $V_{DDQ} * 0.8$

Operating Currents

| Parameter | Symbol | Test Conditions | -300 | | -250 | | -200 | | -167 | | Notes |
|------------------------------|-----------|--|-----------|-------------|-----------|-------------|-----------|-------------|-----------|-------------|-------|
| | | | 0 to 70°C | -40 to 85°C | 0 to 70°C | -40 to 85°C | 0 to 70°C | -40 to 85°C | 0 to 70°C | -40 to 85°C | |
| Operating Current (x36): DDR | I_{DD} | $V_{DD} = \text{Max}$, $I_{OUT} = 0$ mA Cycle Time $\geq t_{KHKH}$ Min | TBD | TBD | TBD | TBD | TBD | TBD | TBD | TBD | 1, 2 |
| Operating Current (x18): DDR | I_{DD} | $V_{DD} = \text{Max}$, $I_{OUT} = 0$ mA Cycle Time $\geq t_{KHKH}$ Min | TBD | TBD | TBD | TBD | TBD | TBD | TBD | TBD | 1, 2 |
| Standby Current (NOP): DDR | I_{SB1} | Device deselected, $I_{OUT} = 0$ mA, $f = \text{Max}$, All Inputs ≤ 0.2 V or $\geq V_{DD} - 0.2$ V | TBD | TBD | TBD | TBD | TBD | TBD | TBD | TBD | 1, 3 |

Notes:

- Minimum cycle, $I_{OUT} = 0$ mA
- Operating current is calculated with 50% read cycles and 50% write cycles.
- Standby Current is only after all pending read and write burst operations are completed.

AC Electrical Characteristics

| Parameter | Symbol | -300 | | -250 | | -200 | | -167 | | Units | Notes |
|--|--|--------|------|--------|------|--------|------|--------|------|-------|-------|
| | | Min | Max | Min | Max | Min | Max | Min | Max | | |
| Clock | | | | | | | | | | | |
| K, \overline{K} Clock Cycle Time C, \overline{C} Clock Cycle Time | t_{KHKH} t_{CHCH} | 3.3 | 8.4 | 4.0 | 8.4 | 5.0 | 8.4 | 6.0 | 8.4 | ns | |
| tKC Variable | t_{KCVar} | — | 0.2 | — | 0.2 | — | 0.2 | — | 0.2 | ns | 6 |
| K, \overline{K} Clock High Pulse Width C, \overline{C} Clock High Pulse Width | t_{KHKL} t_{CHCL} | 1.32 | — | 1.6 | — | 2.0 | — | 2.4 | — | ns | |
| K, \overline{K} Clock Low Pulse Width C, \overline{C} Clock Low Pulse Width | t_{KLKH} t_{CLCH} | 1.32 | — | 1.6 | — | 2.0 | — | 2.4 | — | ns | |
| K to \overline{K} High C to \overline{C} High | $t_{KH\overline{K}H}$ $t_{CH\overline{C}H}$ | 1.49 | — | 1.8 | — | 2.2 | — | 2.7 | — | ns | |
| \overline{K} to K High \overline{C} to C High | $t_{\overline{K}HKH}$ $t_{\overline{C}CHH}$ | 1.49 | — | 1.8 | — | 2.2 | — | 2.7 | — | ns | |
| K, \overline{K} Clock High to C, \overline{C} Clock High | t_{KHCH} | 0 | 1.1 | 0 | 1.1 | 0 | 1.1 | 0 | 1.1 | ns | |
| DLL Lock Time | t_{KCLock} | 65,536 | — | 65,536 | — | 65,536 | — | 65,536 | — | cycle | 7 |
| K Static to DLL reset | $t_{KCRReset}$ | 30 | — | 30 | — | 30 | — | 30 | — | ns | |
| Output Times | | | | | | | | | | | |
| K, \overline{K} Clock High to Data Output Valid C, \overline{C} Clock High to Data Output Valid | t_{KHQV} t_{CHQV} | — | 0.45 | — | 0.45 | — | 0.45 | — | 0.5 | ns | 4 |
| K, \overline{K} Clock High to Data Output Hold C, \overline{C} Clock High to Data Output Hold | t_{KHQX} t_{CHQX} | −0.45 | — | −0.45 | — | −0.45 | — | −0.5 | — | ns | 4 |
| K, \overline{K} Clock High to Echo Clock Valid C, \overline{C} Clock High to Echo Clock Valid | t_{KHCQV} t_{CHCQV} | — | 0.45 | — | 0.45 | — | 0.45 | — | 0.5 | ns | |
| K, \overline{K} Clock High to Echo Clock Hold C, \overline{C} Clock High to Echo Clock Hold | t_{KHCQX} t_{CHCQX} | −0.45 | — | −0.45 | — | −0.45 | — | −0.5 | — | ns | |
| CQ, \overline{CQ} High Output Valid | t_{CQHqV} | — | 0.27 | — | 0.30 | — | 0.35 | — | 0.40 | ns | 8 |
| CQ, \overline{CQ} High Output Hold | t_{CQHqX} | −0.27 | — | −0.30 | — | −0.35 | — | −0.40 | — | ns | 8 |
| CQ Phase Distortion | $t_{CQH\overline{CQH}}$ $t_{\overline{CQH}CQH}$ | 1.24 | — | 1.55 | — | 1.95 | — | 2.45 | — | ns | |
| K Clock High to Data Output High-Z C Clock High to Data Output High-Z | t_{KHQZ} t_{CHQZ} | — | 0.45 | — | 0.45 | — | 0.45 | — | 0.5 | ns | 4 |
| K Clock High to Data Output Low-Z C Clock High to Data Output Low-Z | t_{KHQX1} t_{CHQX1} | −0.45 | — | −0.45 | — | −0.45 | — | −0.5 | — | ns | 4 |
| Setup Times | | | | | | | | | | | |
| Address Input Setup Time | t_{AVKH} | 0.4 | — | 0.5 | — | 0.6 | — | 0.7 | — | ns | 1 |
| Control Input Setup Time (R/ \overline{W}) | t_{IVKH} | 0.4 | — | 0.5 | — | 0.6 | — | 0.7 | — | ns | 2 |
| Control Input Setup Time (BW \overline{X}) | t_{IVKH} | 0.3 | — | 0.35 | — | 0.4 | — | 0.5 | — | ns | 3 |
| Data Input Setup Time | t_{DVKH} | 0.3 | — | 0.35 | — | 0.4 | — | 0.5 | — | ns | |

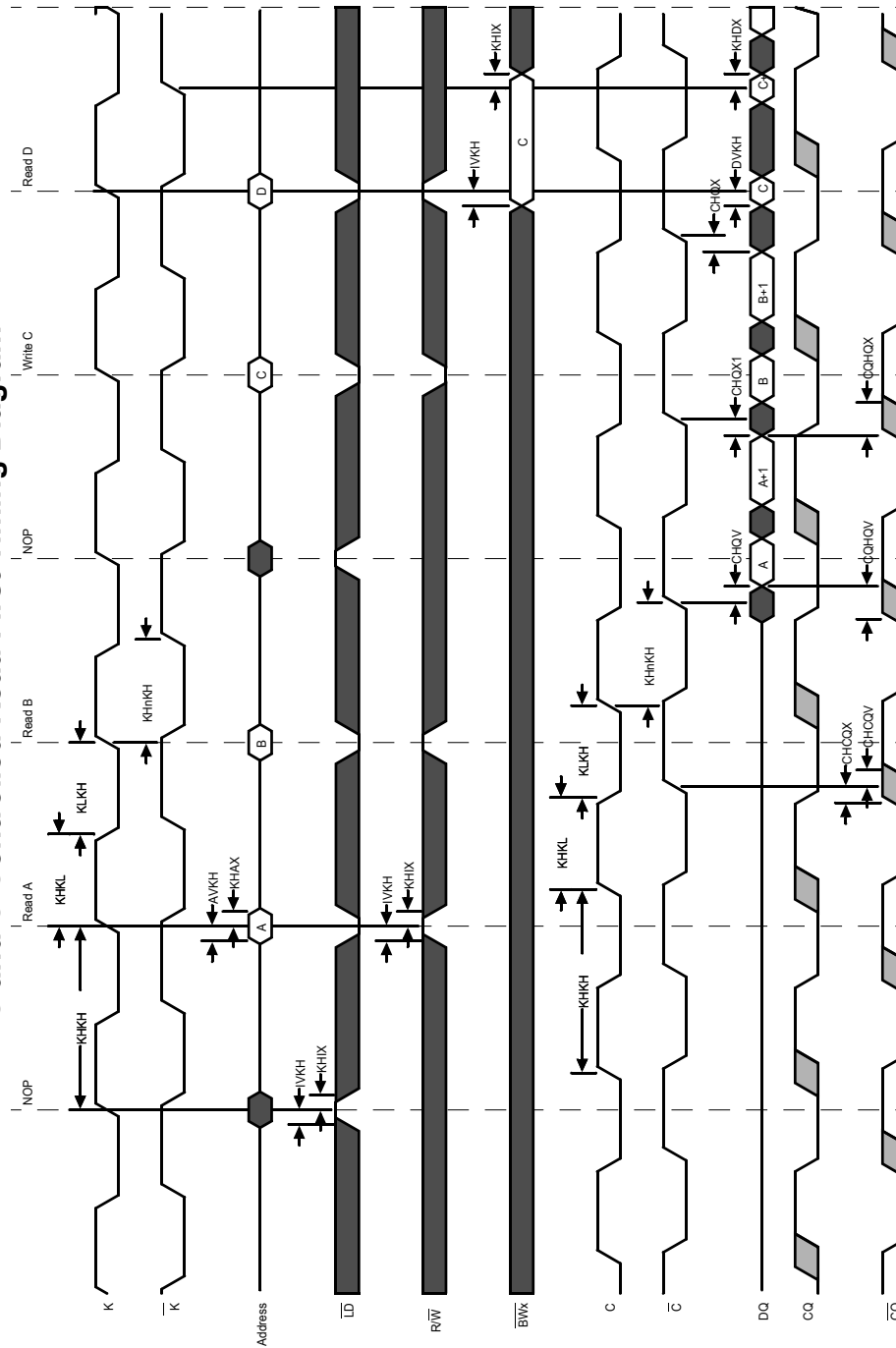
AC Electrical Characteristics

| Parameter | Symbol | -300 | | -250 | | -200 | | -167 | | Units | Notes |
|---|-------------------|------|-----|------|-----|------|-----|------|-----|-------|-------|
| | | Min | Max | Min | Max | Min | Max | Min | Max | | |
| Hold Times | | | | | | | | | | | |
| Address Input Hold Time | t _{KHAX} | 0.4 | — | 0.5 | — | 0.6 | — | 0.7 | — | ns | 1 |
| Control Input Hold Time (R/W) | t _{KHIX} | 0.4 | — | 0.5 | — | 0.6 | — | 0.7 | — | ns | 2 |
| Control Input Setup Time (BW \overline{X}) | t _{IVKH} | 0.3 | — | 0.35 | — | 0.4 | — | 0.5 | — | ns | 3 |
| Data Input Hold Time | t _{KHDX} | 0.3 | — | 0.35 | — | 0.4 | — | 0.5 | — | ns | |

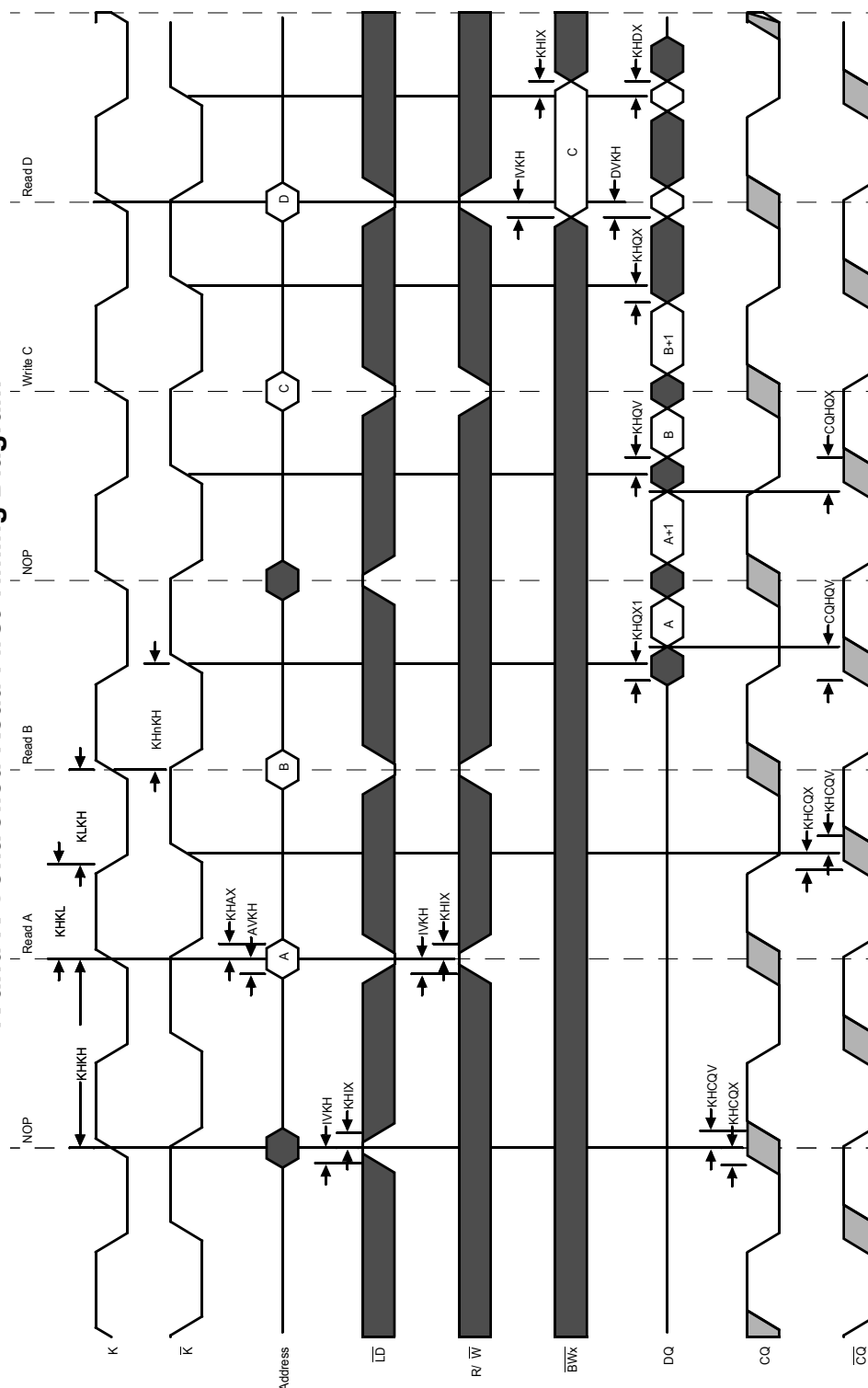
Notes:

1. All Address inputs must meet the specified setup and hold times for all latching clock edges.
2. Control singles are \overline{LD} , R/\overline{W} .
3. Control singles are ($BW2$, $BW3$ for x36).
4. If C , \overline{C} are tied high, K , \overline{K} become the references for C , \overline{C} timing parameters.
5. To avoid bus contention, at a given voltage and temperature t_{CHQX1} is bigger than t_{CHQZ} . The specs as shown do not imply bus contention because t_{CHQX1} is a MIN parameter that is worst case at totally different test conditions (0°C, 1.9 V) than t_{CHQZ} , which is a MAX parameter (worst case at 70°C, 1.7 V). It is not possible for two ECCRAMs on the same board to be at such different voltages and temperatures.
6. Clock phase jitter is the variance from clock rising edge to the next expected clock rising edge.
7. V_{DD} slew rate must be less than 0.1 V DC per 50 ns for DLL lock retention. DLL lock time begins once V_{DD} and input clock are stable.
8. Echo clock is very tightly controlled to data valid/data hold. By design, there is a ± 0.1 ns variation from echo clock to data. The datasheet parameters reflect tester guard bands and test setup variations.

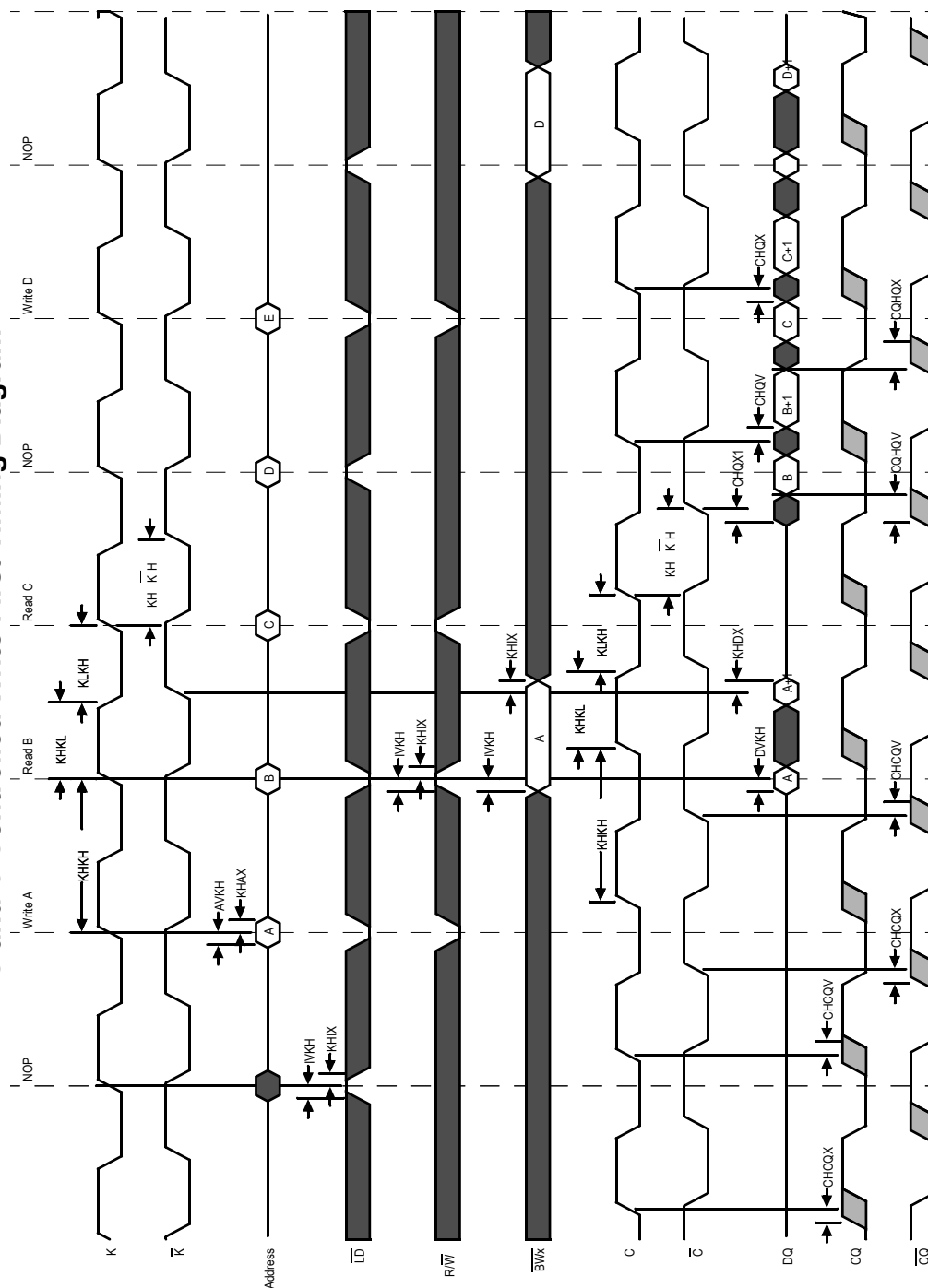
C and C-Controlled Read First Timing Diagram



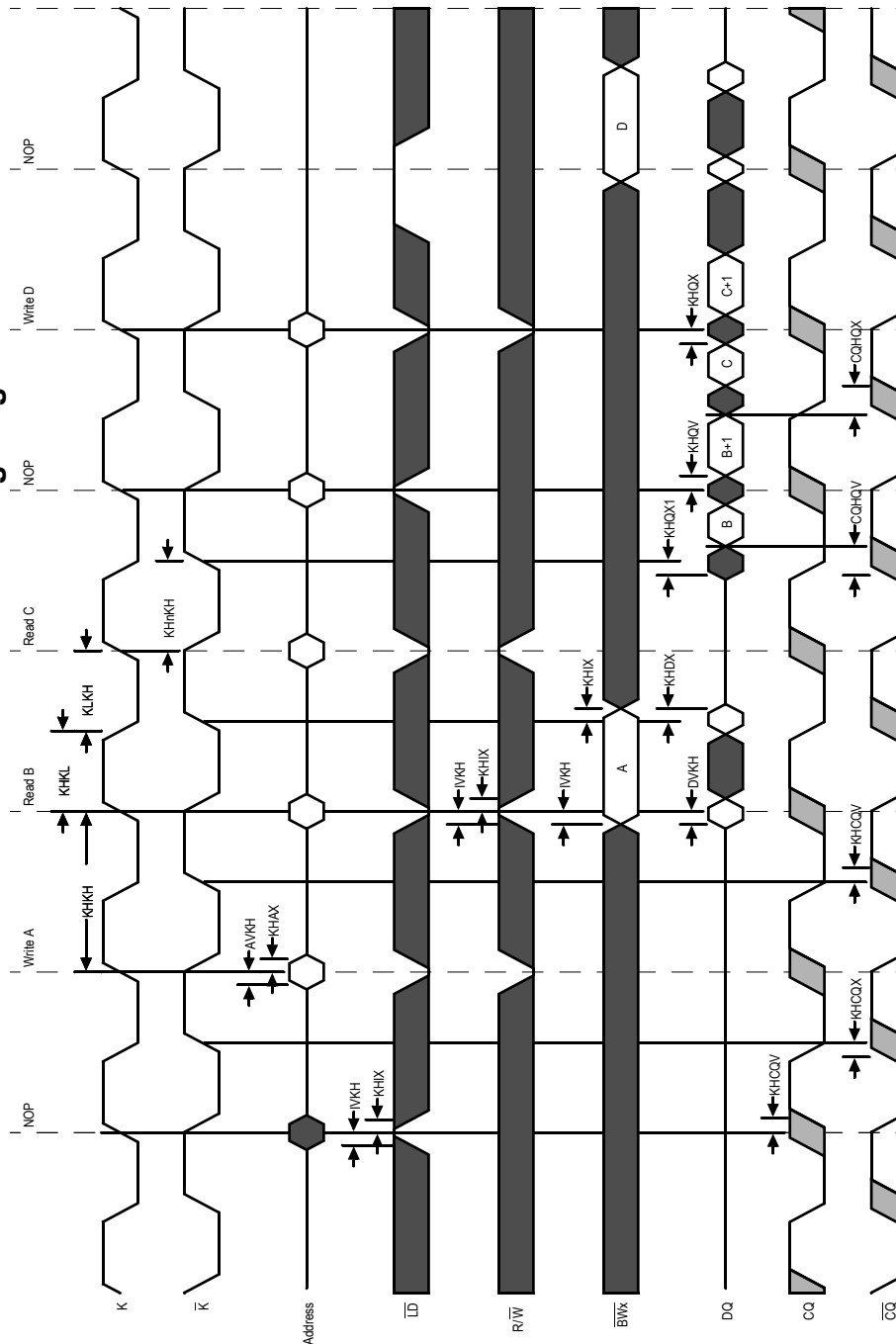
K and K Controlled Read First Timing Diagram



C and C Controlled Write First Timing Diagram



K and K Controlled Write First Timing Diagram



JTAG Port Operation

Overview

The JTAG Port on this RAM operates in a manner that is compliant with IEEE Standard 1149.1-1990, a serial boundary scan interface standard (commonly referred to as JTAG). The JTAG Port input interface levels scale with V_{DD} . The JTAG output drivers are powered by V_{DD} .

Disabling the JTAG Port

It is possible to use this device without utilizing the JTAG port. The port is reset at power-up and will remain inactive unless clocked. TCK, TDI, and TMS are designed with internal pull-up circuits. To assure normal operation of the RAM with the JTAG Port unused, TCK, TDI, and TMS may be left floating or tied to either V_{DD} or V_{SS} . TDO should be left unconnected.

JTAG Pin Descriptions

| Pin | Pin Name | I/O | Description |
|-----|------------------|-----|--|
| TCK | Test Clock | In | Clocks all TAP events. All inputs are captured on the rising edge of TCK and all outputs propagate from the falling edge of TCK. |
| TMS | Test Mode Select | In | The TMS input is sampled on the rising edge of TCK. This is the command input for the TAP controller state machine. An undriven TMS input will produce the same result as a logic one input level. |
| TDI | Test Data In | In | The TDI input is sampled on the rising edge of TCK. This is the input side of the serial registers placed between TDI and TDO. The register placed between TDI and TDO is determined by the state of the TAP Controller state machine and the instruction that is currently loaded in the TAP Instruction Register (refer to the TAP Controller State Diagram). An undriven TDI pin will produce the same result as a logic one input level. |
| TDO | Test Data Out | Out | Output that is active depending on the state of the TAP state machine. Output changes in response to the falling edge of TCK. This is the output side of the serial registers placed between TDI and TDO. |

Note:

This device does not have a TRST (TAP Reset) pin. TRST is optional in IEEE 1149.1. The Test-Logic-Reset state is entered while TMS is held high for five rising edges of TCK. The TAP Controller is also reset automatically at power-up.

JTAG Port Registers

Overview

The various JTAG registers, referred to as Test Access Port or TAP Registers, are selected (one at a time) via the sequences of 1s and 0s applied to TMS as TCK is strobed. Each of the TAP Registers is a serial shift register that captures serial input data on the rising edge of TCK and pushes serial data out on the next falling edge of TCK. When a register is selected, it is placed between the TDI and TDO pins.

Instruction Register

The Instruction Register holds the instructions that are executed by the TAP controller when it is moved into the Run, Test/Idle, or the various data register states. Instructions are 3 bits long. The Instruction Register can be loaded when it is placed between the TDI and TDO pins. The Instruction Register is automatically preloaded with the IDCODE instruction at power-up or whenever the controller is placed in Test-Logic-Reset state.

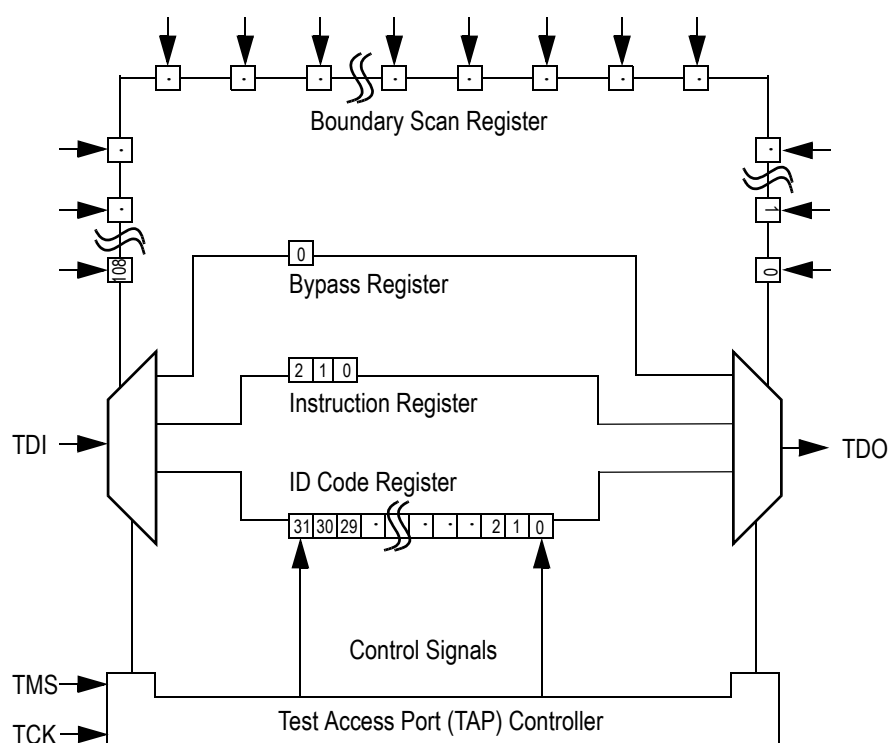
Bypass Register

The Bypass Register is a single bit register that can be placed between TDI and TDO. It allows serial test data to be passed through the RAM's JTAG Port to another device in the scan chain with as little delay as possible.

Boundary Scan Register

The Boundary Scan Register is a collection of flip flops that can be preset by the logic level found on the RAM's input or I/O pins. The flip flops are then daisy chained together so the levels found can be shifted serially out of the JTAG Port's TDO pin. The Boundary Scan Register also includes a number of place holder flip flops (always set to a logic 1). The relationship between the device pins and the bits in the Boundary Scan Register is described in the Scan Order Table following. The Boundary Scan Register, under the control of the TAP Controller, is loaded with the contents of the RAM's I/O ring when the controller is in Capture-DR state and then is placed between the TDI and TDO pins when the controller is moved to Shift-DR state. SAMPLE-Z, SAMPLE/PRELOAD and EXTEST instructions can be used to activate the Boundary Scan Register.

JTAG TAP Block Diagram



Identification (ID) Register

The ID Register is a 32-bit register that is loaded with a device and vendor specific 32-bit code when the controller is put in Capture-DR state with the IDCODE command loaded in the Instruction Register. The code is loaded from a 32-bit on-chip ROM. It describes various attributes of the RAM as indicated below. The register is then placed between the TDI and TDO pins when the controller is moved into Shift-DR state. Bit 0 in the register is the LSB and the first to reach TDO when shifting begins.

ID Register Contents

| | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | | |
|-------|----------|----|----|----|----|----|----|----|----|----|----|----|----|----|----|----|----|----|----|----|---|----|---|---|---|---|---|---|---|---|-------------------|---|
| | Not Used | | | | | | | | | | | | | | | | | | | | GSI Technology JEDEC Vendor ID Code | | | | | | | | | | Presence Register | |
| Bit # | 31 | 30 | 29 | 28 | 27 | 26 | 25 | 24 | 23 | 22 | 21 | 20 | 19 | 18 | 17 | 16 | 15 | 14 | 13 | 12 | 11 | 10 | 9 | 8 | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
| | X | X | X | X | X | X | X | X | X | X | X | X | X | X | X | X | X | X | X | X | 0 | 0 | 0 | 1 | 1 | 0 | 1 | 1 | 0 | 0 | 1 | 1 |

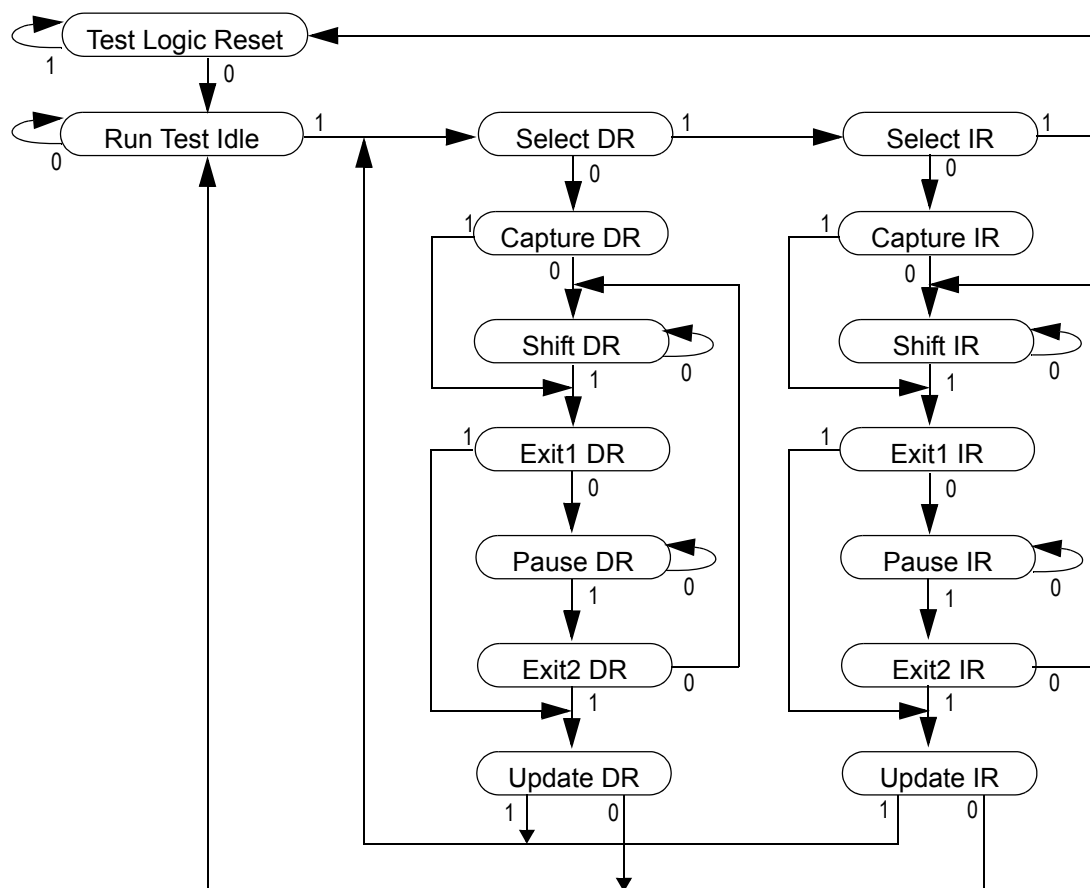
Tap Controller Instruction Set

Overview

There are two classes of instructions defined in the Standard 1149.1-1990; the standard (Public) instructions, and device specific (Private) instructions. Some Public instructions are mandatory for 1149.1 compliance. Optional Public instructions must be implemented in prescribed ways. The TAP on this device may be used to monitor all input and I/O pads, and can be used to load address, data or control signals into the RAM or to preload the I/O buffers.

When the TAP controller is placed in Capture-IR state the two least significant bits of the instruction register are loaded with 01. When the controller is moved to the Shift-IR state the Instruction Register is placed between TDI and TDO. In this state the desired instruction is serially loaded through the TDI input (while the previous contents are shifted out at TDO). For all instructions, the TAP executes newly loaded instructions only when the controller is moved to Update-IR state. The TAP instruction set for this device is listed in the following table.

JTAG Tap Controller State Diagram



Instruction Descriptions

BYPASS

When the BYPASS instruction is loaded in the Instruction Register the Bypass Register is placed between TDI and TDO. This occurs when the TAP controller is moved to the Shift-DR state. This allows the board level scan path to be shortened to facilitate testing of other devices in the scan path.

SAMPLE/PRELOAD

SAMPLE/PRELOAD is a Standard 1149.1 mandatory public instruction. When the SAMPLE / PRELOAD instruction is loaded in the Instruction Register, moving the TAP controller into the Capture-DR state loads the data in the RAMs input and I/O buffers into the Boundary Scan Register. Boundary Scan Register locations are not associated with an input or I/O pin, and are loaded with the default state identified in the Boundary Scan Chain table at the end of this section of the datasheet. Because the RAM clock is independent from the TAP Clock (TCK) it is possible for the TAP to attempt to capture the I/O ring contents while the input buffers are in transition (i.e. in a metastable state). Although allowing the TAP to sample metastable inputs will not harm the device, repeatable results cannot be expected. RAM input signals must be stabilized for long enough to meet the TAPs input data capture set-up plus hold time (t_{TS} plus t_{TH}). The RAMs clock inputs need not be paused for any other TAP operation except capturing the I/O ring contents into the Boundary Scan Register. Moving the controller to Shift-DR state then places the boundary scan register between the TDI and TDO pins.

EXTEST

EXTEST is an IEEE 1149.1 mandatory public instruction. It is to be executed whenever the instruction register is loaded with all logic 0s. The EXTEST command does not block or override the RAM's input pins; therefore, the RAM's internal state is still determined by its input pins.

Typically, the Boundary Scan Register is loaded with the desired pattern of data with the SAMPLE/PRELOAD command. Then the EXTEST command is used to output the Boundary Scan Register's contents, in parallel, on the RAM's data output drivers on the falling edge of TCK when the controller is in the Update-IR state.

Alternately, the Boundary Scan Register may be loaded in parallel using the EXTEST command. When the EXTEST instruction is selected, the state of all the RAM's input and I/O pins, as well as the default values at Scan Register locations not associated with a pin, are transferred in parallel into the Boundary Scan Register on the rising edge of TCK in the Capture-DR state, the RAM's output pins drive out the value of the Boundary Scan Register location with which each output pin is associated.

IDCODE

The IDCODE instruction causes the ID ROM to be loaded into the ID register when the controller is in Capture-DR mode and places the ID register between the TDI and TDO pins in Shift-DR mode. The IDCODE instruction is the default instruction loaded in at power up and any time the controller is placed in the Test-Logic-Reset state.

SAMPLE-Z

If the SAMPLE-Z instruction is loaded in the instruction register, all RAM outputs are forced to an inactive drive state (high-Z) and the Boundary Scan Register is connected between TDI and TDO when the TAP controller is moved to the Shift-DR state.

JTAG TAP Instruction Set Summary

| Instruction | Code | Description | Notes |
|----------------|------|---|-------|
| EXTEST | 000 | Places the Boundary Scan Register between TDI and TDO. | 1 |
| IDCODE | 001 | Preloads ID Register and places it between TDI and TDO. | 1, 2 |
| SAMPLE-Z | 010 | Captures I/O ring contents. Places the Boundary Scan Register between TDI and TDO. Forces all RAM output drivers to High-Z except CQ. | 1 |
| GSI | 011 | GSI private instruction. | 1 |
| SAMPLE/PRELOAD | 100 | Captures I/O ring contents. Places the Boundary Scan Register between TDI and TDO. | 1 |
| GSI | 101 | GSI private instruction. | 1 |
| GSI | 110 | GSI private instruction. | 1 |
| BYPASS | 111 | Places Bypass Register between TDI and TDO. | 1 |

Notes:

1. Instruction codes expressed in binary, MSB on left, LSB on right.
2. Default instruction automatically loaded at power-up and in test-logic-reset state.

JTAG Port Recommended Operating Conditions and DC Characteristics

| Parameter | Symbol | Min. | Max. | Unit | Notes |
|--|------------|----------------|----------------|------|-------|
| Test Port Input Low Voltage | V_{ILJ} | -0.3 | $0.3 * V_{DD}$ | V | 1 |
| Test Port Input High Voltage | V_{IHJ} | $0.7 * V_{DD}$ | $V_{DD} + 0.3$ | V | 1 |
| TMS, TCK and TDI Input Leakage Current | I_{INHJ} | -300 | 1 | uA | 2 |
| TMS, TCK and TDI Input Leakage Current | I_{INLJ} | -1 | 100 | uA | 3 |
| TDO Output Leakage Current | I_{OLJ} | -1 | 1 | uA | 4 |
| Test Port Output High Voltage | V_{OHJ} | $V_{DD} - 0.2$ | — | V | 5, 6 |
| Test Port Output Low Voltage | V_{OLJ} | — | 0.2 | V | 5, 7 |
| Test Port Output CMOS High | V_{OHJC} | $V_{DD} - 0.1$ | — | V | 5, 8 |
| Test Port Output CMOS Low | V_{OLJC} | — | 0.1 | V | 5, 9 |

Notes:

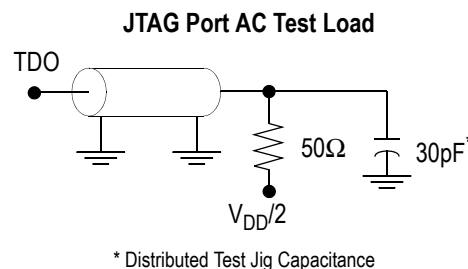
- Input Under/overshoot voltage must be $-1\text{ V} < V_i < V_{DDn} + 1\text{ V}$ not to exceed 2.4 V maximum, with a pulse width not to exceed 20% tTKC.
- $V_{ILJ} \leq V_{IN} \leq V_{DDn}$
- $0\text{ V} \leq V_{IN} \leq V_{ILJn}$
- Output Disable, $V_{OUT} = 0$ to V_{DDn}
- The TDO output driver is served by the V_{DD} supply.
- $I_{OHJ} = -2\text{ mA}$
- $I_{OLJ} = +2\text{ mA}$
- $I_{OHJC} = -100\text{ uA}$
- $I_{OLJC} = +100\text{ uA}$

JTAG Port AC Test Conditions

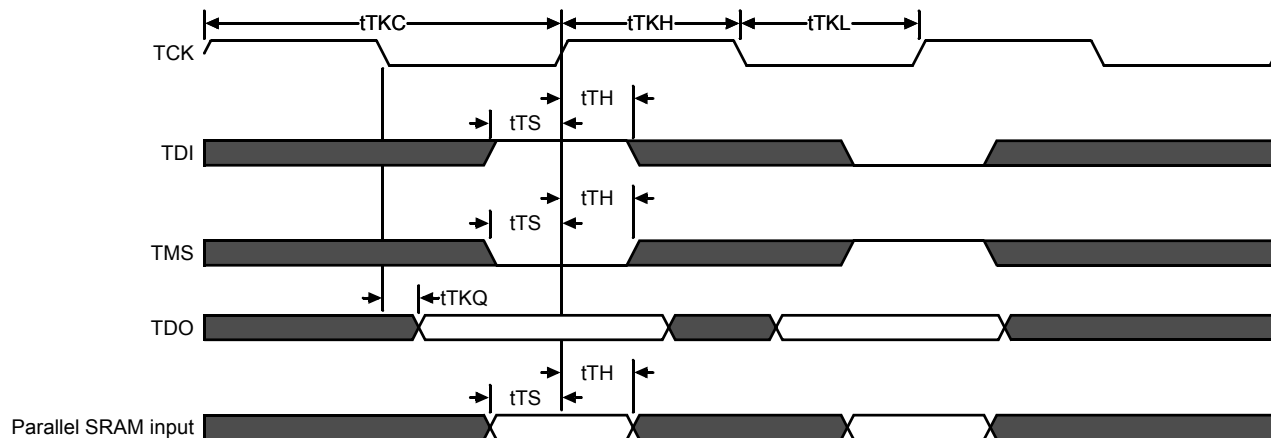
| Parameter | Conditions |
|------------------------|-------------------------|
| Input high level | $V_{DD} - 0.2\text{ V}$ |
| Input low level | 0.2 V |
| Input slew rate | 1 V/ns |
| Input reference level | $V_{DD}/2$ |
| Output reference level | $V_{DD}/2$ |

Notes:

- Include scope and jig capacitance.
- Test conditions as shown unless otherwise noted.



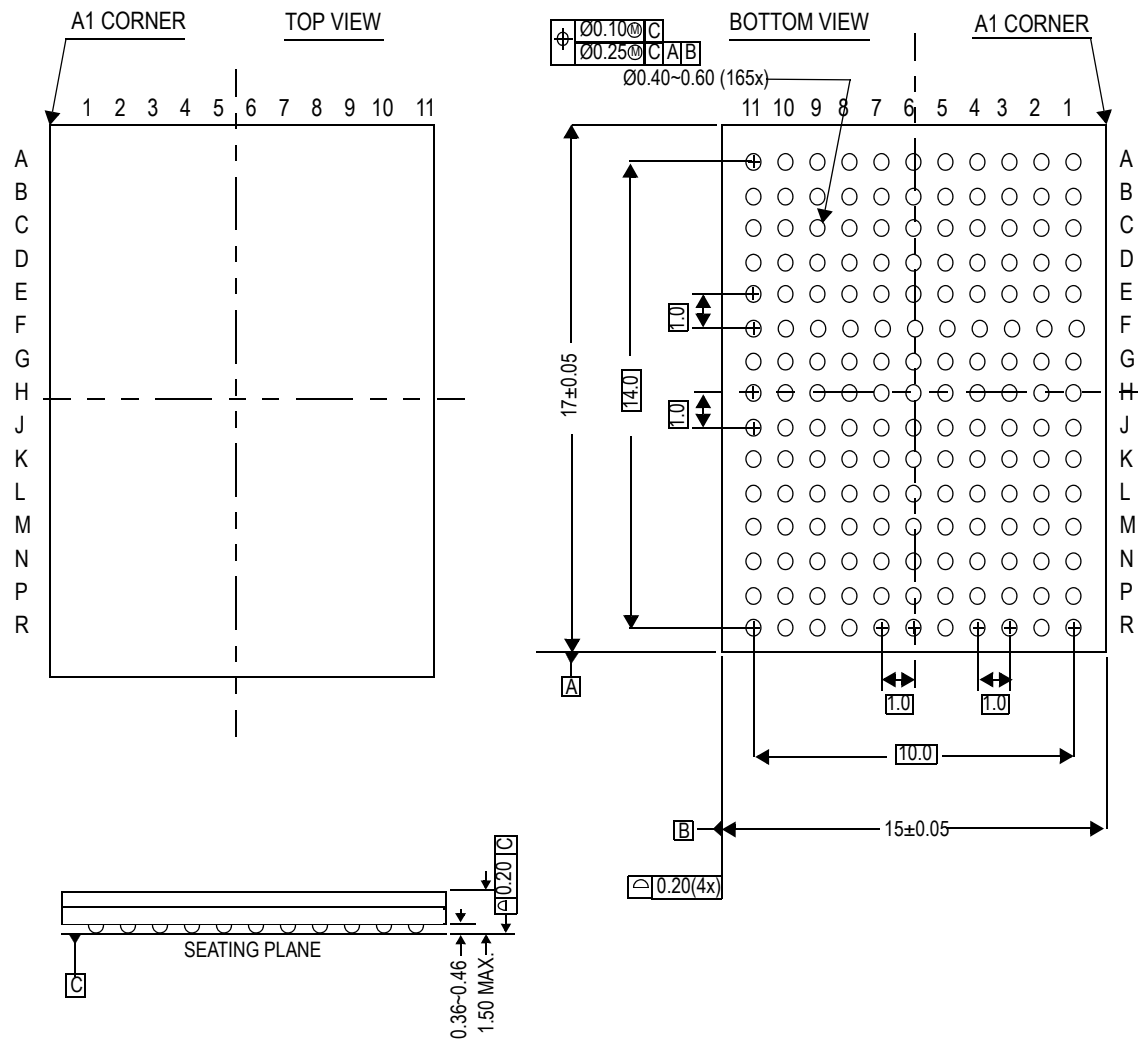
JTAG Port Timing Diagram



JTAG Port AC Electrical Characteristics

| Parameter | Symbol | Min | Max | Unit |
|-----------------------|-----------|-----|-----|------|
| TCK Cycle Time | t_{TKC} | 50 | — | ns |
| TCK Low to TDO Valid | t_{TKQ} | — | 20 | ns |
| TCK High Pulse Width | t_{TKH} | 20 | — | ns |
| TCK Low Pulse Width | t_{TKL} | 20 | — | ns |
| TDI & TMS Set Up Time | t_{TS} | 10 | — | ns |
| TDI & TMS Hold Time | t_{TH} | 10 | — | ns |

Package Dimensions—165-Bump FPBGA (Package E)



Ordering Information—GSI SigmaDDR-II ECCRAM

| Org | Part Number ¹ | Type | Package | Speed (MHz) | T _A ² |
|---------|--------------------------|--------------------|-----------------------------|-------------|-----------------------------|
| 4M x 18 | GS8672T18AE-300 | SigmaDDR-II ECCRAM | 165-bump BGA | 300 | C |
| 4M x 18 | GS8672T18AE-250 | SigmaDDR-II ECCRAM | 165-bump BGA | 250 | C |
| 4M x 18 | GS8672T18AE-200 | SigmaDDR-II ECCRAM | 165-bump BGA | 200 | C |
| 4M x 18 | GS8672T18AE-167 | SigmaDDR-II ECCRAM | 165-bump BGA | 167 | C |
| 4M x 18 | GS8672T18AE-300I | SigmaDDR-II ECCRAM | 165-bump BGA | 300 | I |
| 4M x 18 | GS8672T18AE-250I | SigmaDDR-II ECCRAM | 165-bump BGA | 250 | I |
| 4M x 18 | GS8672T18AE-200I | SigmaDDR-II ECCRAM | 165-bump BGA | 200 | I |
| 4M x 18 | GS8672T18AE-167I | SigmaDDR-II ECCRAM | 165-bump BGA | 167 | I |
| 2M x 36 | GS8672T36AE-300 | SigmaDDR-II ECCRAM | 165-bump BGA | 300 | C |
| 2M x 36 | GS8672T36AE-250 | SigmaDDR-II ECCRAM | 165-bump BGA | 250 | C |
| 2M x 36 | GS8672T36AE-200 | SigmaDDR-II ECCRAM | 165-bump BGA | 200 | C |
| 2M x 36 | GS8672T36AE-167 | SigmaDDR-II ECCRAM | 165-bump BGA | 167 | C |
| 2M x 36 | GS8672T36AE-300I | SigmaDDR-II ECCRAM | 165-bump BGA | 300 | I |
| 2M x 36 | GS8672T36AE-250I | SigmaDDR-II ECCRAM | 165-bump BGA | 250 | I |
| 2M x 36 | GS8672T36AE-200I | SigmaDDR-II ECCRAM | 165-bump BGA | 200 | I |
| 2M x 36 | GS8672T36AE-167I | SigmaDDR-II ECCRAM | 165-bump BGA | 167 | I |
| 4M x 18 | GS8672T18AGE-300 | SigmaDDR-II ECCRAM | RoHS-compliant 165-bump BGA | 300 | C |
| 4M x 18 | GS8672T18AGE-250 | SigmaDDR-II ECCRAM | RoHS-compliant 165-bump BGA | 250 | C |
| 4M x 18 | GS8672T18AGE-200 | SigmaDDR-II ECCRAM | RoHS-compliant 165-bump BGA | 200 | C |
| 4M x 18 | GS8672T18AGE-167 | SigmaDDR-II ECCRAM | RoHS-compliant 165-bump BGA | 167 | C |
| 4M x 18 | GS8672T18AGE-300I | SigmaDDR-II ECCRAM | RoHS-compliant 165-bump BGA | 300 | I |
| 4M x 18 | GS8672T18AGE-250I | SigmaDDR-II ECCRAM | RoHS-compliant 165-bump BGA | 250 | I |
| 4M x 18 | GS8672T18AGE-200I | SigmaDDR-II ECCRAM | RoHS-compliant 165-bump BGA | 200 | I |
| 4M x 18 | GS8672T18AGE-167I | SigmaDDR-II ECCRAM | RoHS-compliant 165-bump BGA | 167 | I |
| 2M x 36 | GS8672T36AGE-300 | SigmaDDR-II ECCRAM | RoHS-compliant 165-bump BGA | 300 | C |
| 2M x 36 | GS8672T36AGE-250 | SigmaDDR-II ECCRAM | RoHS-compliant 165-bump BGA | 250 | C |
| 2M x 36 | GS8672T36AGE-200 | SigmaDDR-II ECCRAM | RoHS-compliant 165-bump BGA | 200 | C |
| 2M x 36 | GS8672T36AGE-167 | SigmaDDR-II ECCRAM | RoHS-compliant 165-bump BGA | 167 | C |
| 2M x 36 | GS8672T36AGE-300I | SigmaDDR-II ECCRAM | RoHS-compliant 165-bump BGA | 300 | I |

Notes:

- For Tape and Reel add the character "T" to the end of the part number. Example: GS8672Tx36AE-300T.
- C = Commercial Temperature Range. I = Industrial Temperature Range.

Ordering Information—GSI SigmaDDR-II ECCRAM

| Org | Part Number ¹ | Type | Package | Speed (MHz) | T _A ² |
|---------|--------------------------|--------------------|-----------------------------|-------------|-----------------------------|
| 2M x 36 | GS8672T36AGE-250I | SigmaDDR-II ECCRAM | RoHS-compliant 165-bump BGA | 250 | I |
| 2M x 36 | GS8672T36AGE-200I | SigmaDDR-II ECCRAM | RoHS-compliant 165-bump BGA | 200 | I |
| 2M x 36 | GS8672T36AGE-167I | SigmaDDR-II ECCRAM | RoHS-compliant 165-bump BGA | 167 | I |

Notes:

1. For Tape and Reel add the character "T" to the end of the part number. Example: GS8672Tx36AE-300T.
2. C = Commercial Temperature Range. I = Industrial Temperature Range.

GSi SigmaDDR-II ECCRAM Revision History

| Rev. Code: Old; New | Types of Changes Format or Content | Revisions |
|----------------------------|---|---|
| GS8672TxAE_r1 | Format | <ul style="list-style-type: none">• Creation of new datasheet• (Rev1.00a: corrected note citations in Programmable Impedance table on page 14) |